

C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

18. (three times amended) A method of forming a silicon oxide having Si-F bonds, comprising:

providing a reaction chamber at a temperature in excess of 400 degrees Celsius (°C) but less than 700°C;

positioning a substrate within the reaction chamber;

providing an ozone comprising reactant and a precursor having Si-F bonds to the substrate within the reaction chamber and maintaining a pressure within the reaction chamber of from about 400 Torr to about 1 atmosphere;

while providing the ozone comprising reactant and the precursor having Si-F bonds to the substrate, providing a plasma within the reaction chamber; and

causing a silicon oxide having Si-F bonds, to deposit onto the substrate within the reaction chamber at a rate of from about 1000 angstroms per minute (Å/min) to about 10000 Å/min.

38. (twice amended) The method of claim 18 comprising maintaining a temperature within the reaction chamber in excess of 500°C but less than 700°C during the depositing.

43. (twice amended) The method of claim 18 comprising maintaining a temperature within the reaction chamber from about 500°C to about but less than 700°C during the depositing.